BroadBand Silicon Capacitor BBSC492.510 0201M 10nF BV11 Rev. 2.01

General description

BBSC Capacitor targets Optical communication system such as ROSA/TOSA, SONET and all optoelectronics as well as High speed data system or products. The BBSC is suitable for DC blocking, feedback, coupling and bypassing applications in all broadband optoelectronics and High-speed data system. The unique technology of integrated passive device in silicon, developed by Murata Integrated Passive Solutions, offers unique performances with low insertion loss, low reflection and phase stability from 160 KHz to 40 GHz.

These capacitors in ultra-deep trenches in silicon have been developed in a semiconductor process, in order to integrate trench MOS capacitor providing high capacitance value of 10 nF (for kHz–MHz range) and high frequency MIM capacitors for low capacitance value (for GHz range), combined in a 0201M [0.6x0.3mm] case.

The BBSC capacitor provides very high stability of the capacitance over temperature, voltage variation as well as a very high reliability. BBSC capacitors have an extended operating temperature ranging from -55 to 150°C, with very low capacitance change over temperature (+70ppm/K).

<u>Assembly:</u> Suitable for surface mounted application on rigid PCB, ceramic substrate, FR4 (laminate) or flex platforms.

Bump finishing: SAC305 type 6.

Copper pads optional for embedding version and ENIG for un-bumped version, as an optional finishing.

Key features

- Broadband performance up to 40 GHz
- Resonance free
- Phase stability
- Insertion loss < 0.3dB Typ. up to 40 GHz.
- Ultra-high stability of capacitance value:
 - Temperature 70ppm/K (-55 °C to +150 °C)
 - Voltage <0.1%/Volt
 - Negligible capacitance loss through ageing

- Low profile: 140 μm including bump height
- Break down voltage: 11V
- Low leakage current < 100pA
- High reliability
- High operating temperature (up to 150 °C)
- Compatible with high temperature cycling during manufacturing operations (exceeding 300 °C)
- Compatible with EIA 0201 footprint
- SAC305 40µm bumps after reflow

Key applications

- ROSA/TOSA
- SONET
- High speed digital logic

- Microwave/millimetre system
- High volumetric efficiency (i.e. capacitance per unit volume)
- · Broadband test equipment





Functional diagram

The next figure provides implementation set-up diagram.

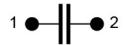


Figure 1 Block Diagram

Electrical performances

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
С	Capacitance value	@+25°C	-	10	-	nF
ΔC_P	Capacitance tolerance (1)	@+25°C	-15	-	+15	%
T _{OP}	Operating temperature		-55	20	150	°C
T _{STG}	Storage temperature (2)		-70		165	°C
ΔC_{T}	Capacitance temperature variation	-55 °C to 150 °C	-	70	-	ppm/K
RV_{DC}	Rated voltage (3)		-	-	3.8 ⁽⁴⁾ 3.4 ⁽⁵⁾	V_{DC}
BV	Break down voltage	@+25°C	11	-	-	V
ΔC_{RVDC}	Capacitance voltage variation	From 0 V to RV _{DC} , @+25°C	-	-	0.1	%/V _{DC}
IR	Insulation resistor	@RV _{DC} , +25°C, 120s	-	10	-	GΩ
ESL	Equivalent Serial Inductance ⁽⁶⁾	@+25°C, SRF shunt mode	-	100	-	рН
ESR	Equivalent Serial Resistance ⁽⁶⁾	@+25°C, shunt mode	-	300	-	mOhm
Fc-3dB	Cut-off frequency at 3dB ⁽⁶⁾	@+25°C	-	160	187	kHz
IL	Insertion loss ⁽⁶⁾	@ 20 GHz, +25°C	-	0.2	-	dB
IL .	IIISCIUOII IOSS	@ 40 GHz, +25°C	-	0.3	-	dB
RL	Return loss ⁽⁶⁾	Up to 40 GHz, +25°C	25	-	-	dB
ESD	HBM stress (7)	JS-001-2017	8	-	-	kV

Table 1 - Electrical performances

^{(7):} please refer to application note 'ESD Challenge in 3D Murata Integrated Passive technology'.



^{(1):} other tolerance available upon request.

^{(2):} without packaging.

^{(3):} Lifetime is voltage and temperature dependent, please refer to application note 'Lifetime of 3D capacitors'.

^{(4): 10} years of intrinsic life time prediction at 100°C continuous operation.

^{(5): 10} years of intrinsic life time prediction at 150°C continuous operation.

^{(6):} Measured.



Module S-parameters of 10nF BBSC in transmission mode

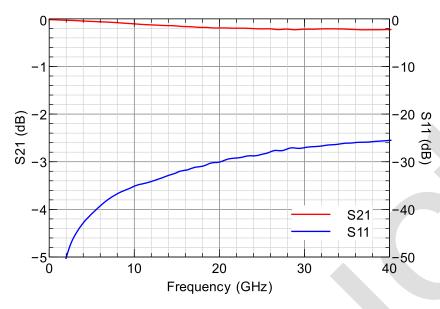


Figure 2 - 10nF BBSC measurement results (module of S-parameters)

Schematic of 10nF BBSC in transmission mode

BBSC492.510 50Ω

<u>4-mil Rogers 4350B.</u>
Microstrip mode – line width = 0.200mm and gap = 0.200 mm. (nominal 50 ohm characteristic impedance).

Figure 3 - 10nF BBSC measurement schematic

Example of surface mounted 0201M

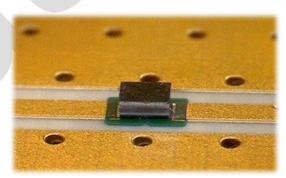


Figure 4 – micro picture of BBSC mounted on board in coplanar mode



Pinning definition

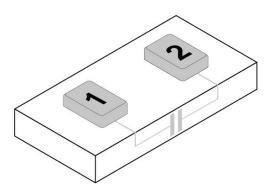


Figure 5 Pin configuration

pin #	Symbol	Coordinates X / Y
1	Signal	-150.0 / 0.0
2	Signal	150.0 / 0.0

Table 2 - Pining description. Reference (0,0) located at the centre of the die.

Ordering Information for BBSC492.510

Regardless of packaging, Murata Integrated Passive Devices delivers products with AQL level II (0.65).

Type number	Package					
(15NC)	Packaging	Finishing	Description			
939114492510-F1S	6" film frame carrier ⁽¹⁾	SAC ⁽²⁾	BBSC 0201M - 10nF - 2 pads - 0.6 x 0.3 mm x 0.10mm ⁽⁴⁾			
939114492510-T3S	7" T&R (1 000 pieces/reel) ⁽³⁾	SAC ⁽²⁾	BBSC 0201M - 10nF - 2 pads - 0.6 x 0.3 mm x 0.10mm (4)			
939114492510-T3N	7" T&R (1 000 pieces/reel) ⁽³⁾	ENIG ⁽²⁾	BBSC 0201M - 10nF - 2 pads - 0.6 x 0.3 mm x 0.10mm ⁽⁴⁾			

- (1) Other Film Frame Carrier are possible on request
- (2) ENIG (0.1μm Au / 5μm Ni) + SAC305 type 6
 (3) Missing capacitors can reach 0.5%
- (4) Refer to Figure 7

Table 3 - Packaging and ordering information

Product Name	Die Name	Description
BBSC492.510	XM0201510	BBSC 10nF/0201M/BV11 - 2 pads - 0.6 x 0.3 x 0.10 mm

Table 4 - Die information





Pad Metallization

This surface mounted Silicon Capacitor is delivered as standard with SAC305 bumping.

Other Metallization, such as ENIG, Copper, Thick Gold or Aluminum pads are possible on request.

Silicon dies are not sensitive to humidity, please refer to applications notes 'Assembly Notes' section 'Handling precautions and storage'.

Material regulation

This product is RoHS compliant at the time of publication. For further information about regulation compliancy, please ask your sales representative.

Package outline

The product is delivered as a bare silicon die.

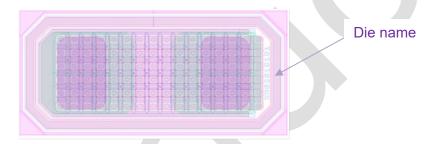


Figure 6 - Layout view

L (mm)	W (mm)	T (mm)	c (mm)	p (mm)	e (mm)	t (mm)
0.60 ±0.02	0.30 ±0.02	0.10 ±0.01	0.10	0.20	0.15	0.04 ⁽¹⁾ 0.05 ⁽²⁾ 0.00 ⁽³⁾

- (1) Standard with solder joint height after reflow on board.
 (2) Standard with solder bump height before assembly

Table 5 - Dimensions and tolerances

⁽³⁾ Only in case of ENIG finishing



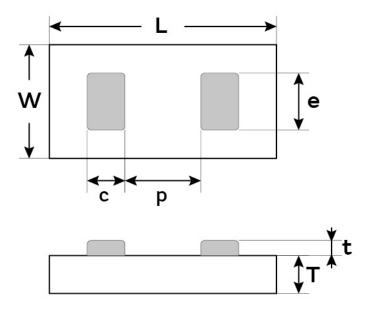


Figure 7 - Package outline drawing

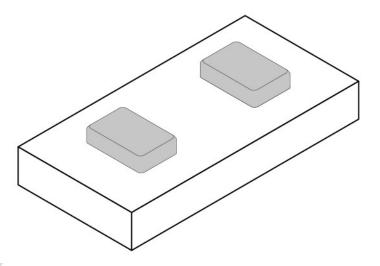


Figure 8 Isometric view

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Assembly

BBSC series is compatible with standard reflow technology.

It is recommended to design mirror pads on the PCB.

For further information, please see our mounting application note

The attachment techniques recommended by Murata on the customer's substrates are fully detailed in specific documents available on our website. To assure the correct use and proper functioning of Murata capacitors please download the assembly instructions on https://www.murata.com/en-us/products/capacitor/siliconcapacitors and read them carefully.



Figure 9 Scan this QR Code to access the Murata Silicon Capacitor web page





Packaging format

Please refer to application note 'Products Storage Conditions and Shelf Life'.

<u>Tape and Reel</u>: Dies are flipped in the tape cavity (bump down) with die ID located near the driving holes of the tape.

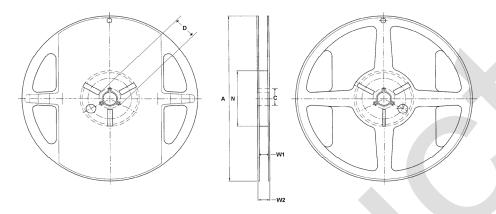


Figure 10 - Reel drawing

Tape Width	Diameter A	С	D	Hub N	W 1	W2
8	178 (7 inches)	13.5	21	60	9.5	11.4

Table 6 - Reel dimensions (mm)

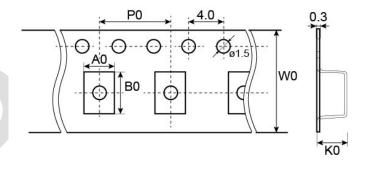


Figure 11 - Tape drawing

Cav	ity dimensio	ns	Carrier	Carrier tape	Reel Capacity	
Ao (*)	Bo ^(*)	Ko ^(*)	tape width W0	pitch P0		
0.36 0.38	0.66 0.68	0.20 0.21	8.00	2.00	1000	

Table 7 - Tape dimensions (mm)

(*) A0, B0 and K0 dimensions depends on the Packaging subcontractor.

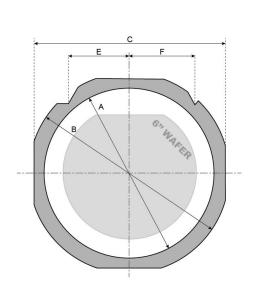




Film frame carrier:

With UV curable dicing tape (UV performed)

Good dies are identified using the SINF electronic mapping format. No ink is added on wafer to label other dies.



E F

Figure 12 FF070 Frame with a 6" wafer

Figure 13 FF108 Frame with a 6" wafer

Frame Reference	Frame Style	Inside diameter A	Outside diameter B	Width C	Thickness	Pin location E	Pin location F
FF070 ⁽¹⁾	DTF-2-6-1	7.638"	8.976"	8.346"	0.048"	2.370"	2.5"
FF108 ⁽¹⁾	DTF-2-8-1	9.842"	11.653"	10.866"	0.048"	2.381"	2.5"

Table 8 - Frame dimensions (inches)

(1) or equivalent



Expander grip ring 6" diameter:

With UV curable dicing tape (UV not performed)

Good dies are identified using the SINF electronic mapping format. No ink is added on wafer to label other dies.

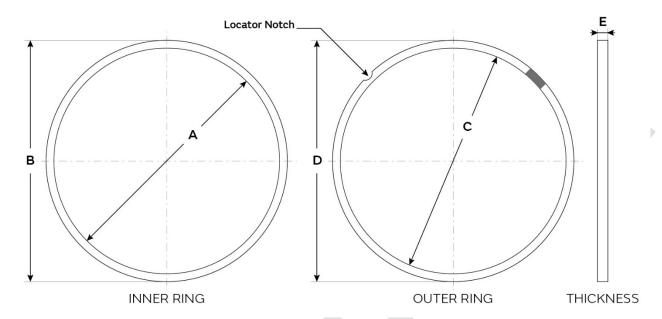


Figure 14 - Grip Ring drawing

Grip Ring Style	А	В	С	D	E	Locator Notch
GRP-2620-6 (1)	7.670"	7.973"	7.975"	8.280"	0.236"	None

Table 9 - Frame dimensions (inches)

(1) or equivalent





Definitions

Data sheet status

Objective specification: This data sheet contains target or goal specifications for product development.

Preliminary specification: This data sheet contains preliminary data; supplementary data may be published later.

Product specification: This data sheet contains final product specifications.

Limiting values: Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those given in the Electrical performances sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information: Where application information is given, it is advisory and does not form part of the specification.

Revision history

Revision	Date	Description	Author.
Release 1.00	2016 February 18 th	Objective specification	OGA
Release 2.00	2020 March 19 th	Update and new template	SCA; CGU; LLE; SJA
Release 2.01	2020 Septembre 17 th	Packaging update	SCA; OGA

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